

15W Power Packaged Transistor

GaN HEMT on SiC

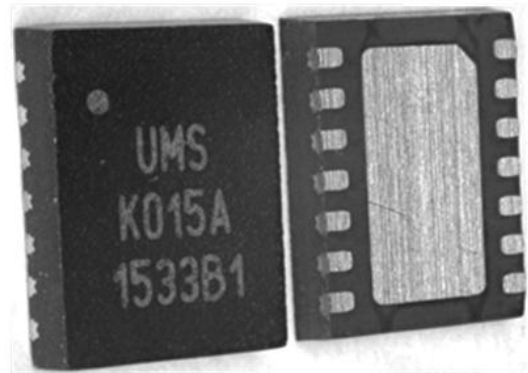
Description

The CHK015A-QIA is an unmatched packaged Gallium Nitride High Electron Mobility Transistor.

It offers general purpose and broadband solutions for a variety of RF power applications. It is well suited for multi-purpose applications such as radar and telecommunication.

The CHK015A-QIA is developed on a 0.5 μ m gate length GaN HEMT process. It requires an external matching circuitry.

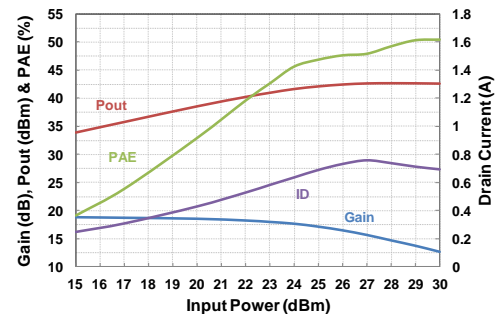
It is proposed in low cost plastic package providing low parasitic and low thermal resistance.



Main Features

- Wide band capability: up to 6GHz
- Pulsed and CW operating modes
- High power: > 15W
- High Efficiency: up to 70%
- DC bias: Vd=50Volt @ Id=100mA
- Low cost package: 14L-DFN3x4
- MTTF > 10⁶ hours @ Tj=200°C

V_{DS} = 50V, I_{D_Q} = 100mA, Freq = 2.9GHz
Pulsed mode (100 μ s, 10%)



Performances on S-band Evaluation Board

Main Electrical Characteristics

T_{case}= +25°C, Pulsed mode, F = 3GHz, V_{DS}=50V, I_{D_Q}=100mA

Symbol	Parameter	Min	Typ	Max	Unit
Gain	Linear Gain	18	20		dB
Pout	Output Power	15	20		W
PAE	Max Power Added Efficiency		60		%
G _{PAE_MAX}	Associated Gain at Max PAE		16		dB

Recommended DC Operating Ratings

T_{case}= +25°C

Symbol	Parameter	Min	Typ	Max	Unit	Conditions
V _{DS}	Drain to Source Voltage			50	V	
V _{GS_Q}	Gate to Source Voltage		-1.9		V	V _D =50V. I _{D_Q} =100mA
I _{D_Q}	Quiescent Drain Current		0.1	0.35	A	V _D =50V
I _{D_MAX}	Drain Current		0.65	(1)	A	V _D =50V. compressed mode
I _{G_MAX}	Gate Current (forward mode)		0	24	mA	Compressed mode
T _{J_MAX}	Junction temperature ⁽¹⁾			200	°C	

⁽¹⁾ Power dissipation must be considered

DC Characteristics

T_{case}= +25°C

Symbol	Parameter	Min	Typ	Max	Unit	Conditions
V _P	Pinch-Off Voltage	-3	-2	-1	V	V _D =50V. I _D = I _{DSS} /100
I _{D_SAT}	Saturated Drain Current		2.7 ⁽¹⁾		A	V _D =7V. V _G =2V
I _{G_leak}	Gate Leakage Current (reverse mode)	-0.8			mA	V _D =50V. V _G =-7V
V _{BDS}	Drain-Source Break-down Voltage		180		V	V _G =-7V. I _D =20mA
R _{TH}	Thermal Resistance ⁽²⁾		6		°C/W	CW

⁽¹⁾ For information, limited by I_{D_MAX}. see on Absolute Maximum Ratings

⁽²⁾ CW mode, reference = package back-side

RF Characteristics

T_{case}= +25°C. Pulsed mode

Symbol	Parameter	Min	Typ	Max	Unit	Conditions
G _{SS}	Small Signal Gain @ 3GHz	18	20		dB	V _D =50V. I _{D_Q} =100mA
	Small Signal Gain @ 6GHz	11	13		dB	
P _{SAT}	Saturated Output Power	15	20		W	V _D =50V. I _{D_Q} =100mA
PAE	Max PAE @ 3GHz		60		%	V _D =50V. I _{D_Q} =100mA
	Max PAE @ 6GHz		50		%	
G _{PAE_MAX}	Associated Gain at Max PAE @ 3GHz @ 6GHz		16		dB	V _D =50V. I _{D_Q} =100mA
			9		dB	

These values are the intrinsic performance of the packaged device. They are deduced from measurements and simulations. They are considered in the reference plane defined by the leads of the package, at the connection interface with the PCB.

The typical performance achievable in more than 10% frequency band around 3GHz was demonstrated using the reference board 61502522 presented hereafter.

Absolute Maximum Ratings

$T_{case} = +25^{\circ}\text{C}^{(1)} \text{ }^{(2)} \text{ }^{(3)}$

Symbol	Parameter	Rating	Unit	Note
V_{DS}	Drain-Source Biasing Voltage	60	V	
V_{GS_Q}	Gate-Source Biasing Voltage	-10. +2	V	
I_{G_MAX}	Maximum Gate Current (forward mode)	48	mA	
I_{G_MIN}	Minimum Gate Current (reverse mode)	-2	mA	
I_{D_MAX}	Maximum Drain Current	2	A	(4)
P_{IN}	Maximum Input Power			(5)
T_j	Junction Temperature	220	$^{\circ}\text{C}$	
T_{STG}	Storage Temperature	-55 to +150	$^{\circ}\text{C}$	
T_{Case}	Case Operating Temperature	See note	$^{\circ}\text{C}$	(4)

⁽¹⁾ Operation of this device above anyone of these parameters may cause permanent damage.

⁽²⁾ Duration < 1s.

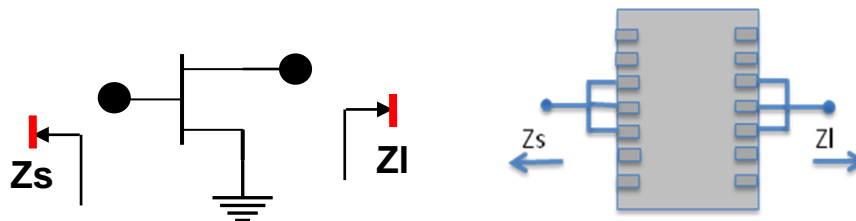
⁽³⁾ The given values must not be exceeded at the same time even momentarily for any parameter, since each parameter is independent from each other. Otherwise deterioration or destruction of the device may take place.

⁽⁴⁾ Max junction temperature must be considered

⁽⁵⁾ Linked to and limited by I_{G_MAX} & I_{G_MIN} values. Maximum input power depends on frequency.

Simulated Source and Load Impedances

$V_{DS} = 50\text{V}$. $I_{D_Q} = 100\text{mA}$



Frequency (MHz)	Z_s	Z_l	Pout (W)	PAE (%)
1000	$2.96 + j13.07$	$39.21 + j33.14$	21.16	66.69
2000	$1.67 + j3.96$	$18.07 + j24.40$	20.88	64.09
3000	$1.79 - j0.80$	$11.08 + j17.47$	20.68	61.61
4000	$1.57 - j4.15$	$6.76 + j10.26$	20.40	58.47
5000	$1.68 - j7.33$	$4.70 + j5.82$	19.92	56.04
6000	$2.04 - j10.45$	$4.05 + j2.61$	19.32	52.49

The impedances are chosen as a trade-off between Output Power, PAE and Stability of the device. These values are given in the reference plane defined by the connection between the transistor leads and the PCB according to the footprint above mentioned

Typical Simulated Package Sij parameters

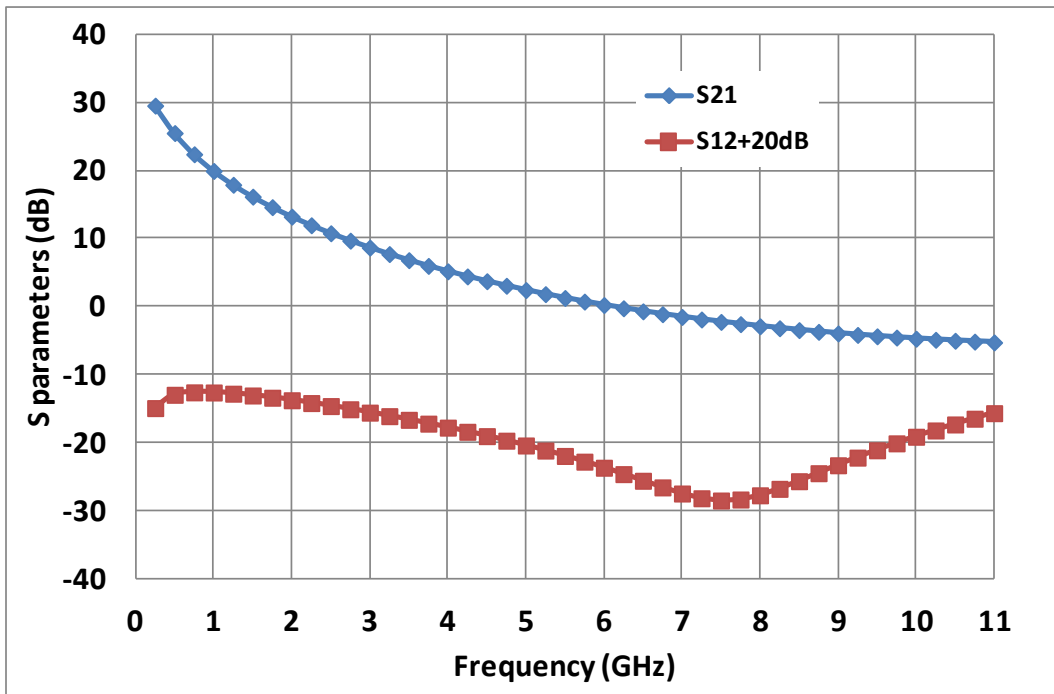
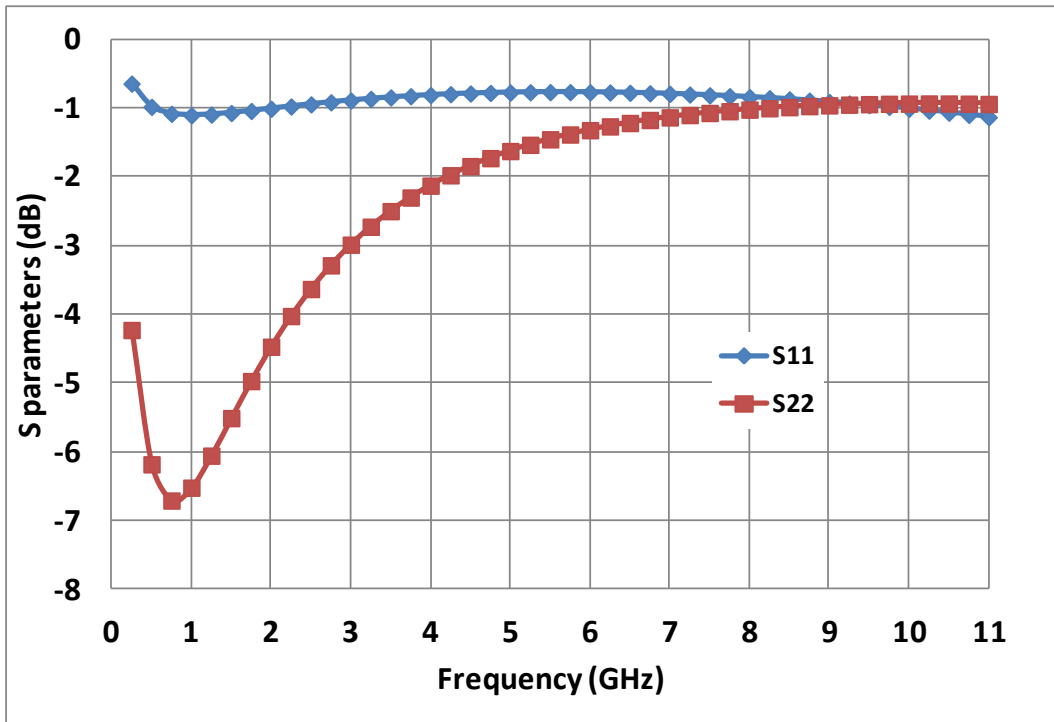
Tamb. = +25°C. V_{DS} = 50V. I_{D,Q} = 100mA

Freq (GHz)	S11 (dB)	PhS11 (°)	S12 (dB)	PhS12 (°)	S21 (dB)	PhS21 (°)	S22 (dB)	PhS22 (°)
0.25	0.930	-86.7	0.018	38.8	30.010	129.0	0.610	-44.6
0.50	0.890	-125.0	0.022	16.0	18.860	104.5	0.490	-65.2
0.75	0.880	-142.9	0.023	3.1	13.170	90.3	0.460	-77.7
1.00	0.880	-153.1	0.023	-6.0	9.930	80.0	0.470	-87.5
1.25	0.880	-159.8	0.023	-13.2	7.860	71.6	0.500	-95.9
1.50	0.880	-164.8	0.022	-19.4	6.420	64.3	0.530	-103.2
1.75	0.890	-168.7	0.021	-24.8	5.380	57.7	0.560	-109.9
2.00	0.890	-171.9	0.020	-29.6	4.580	51.7	0.600	-115.8
2.25	0.890	-174.7	0.019	-33.9	3.960	46.1	0.630	-121.3
2.50	0.900	-177.2	0.019	-37.9	3.460	40.9	0.660	-126.3
2.75	0.900	-179.6	0.018	-41.5	3.050	36.0	0.680	-130.9
3.00	0.900	178.3	0.017	-44.7	2.710	31.5	0.710	-135.2
3.25	0.900	176.2	0.016	-47.7	2.430	27.1	0.730	-139.2
3.50	0.910	174.2	0.015	-50.4	2.190	23.0	0.750	-142.9
3.75	0.910	172.3	0.014	-52.8	1.990	19.0	0.770	-146.4
4.00	0.910	170.5	0.013	-54.9	1.810	15.3	0.780	-149.7
4.25	0.910	168.6	0.012	-56.7	1.660	11.7	0.800	-152.8
4.50	0.910	166.8	0.011	-58.3	1.530	8.2	0.810	-155.8
4.75	0.910	165.1	0.010	-59.6	1.420	4.8	0.820	-158.7
5.00	0.910	163.3	0.009	-60.5	1.320	1.6	0.830	-161.4
5.25	0.910	161.6	0.009	-61.0	1.230	-1.6	0.840	-164.0
5.50	0.910	159.8	0.008	-61.0	1.150	-4.7	0.850	-166.5
5.75	0.910	158.0	0.007	-60.5	1.090	-7.7	0.850	-168.9
6.00	0.910	156.3	0.007	-59.2	1.020	-10.6	0.860	-171.3
6.25	0.910	154.5	0.006	-57.0	0.970	-13.5	0.860	-173.6
6.50	0.910	152.7	0.005	-53.6	0.920	-16.4	0.870	-175.9
6.75	0.910	150.9	0.005	-48.6	0.880	-19.2	0.870	-178.1
7.00	0.910	149.1	0.004	-41.6	0.840	-22.0	0.880	179.8
7.25	0.910	147.2	0.004	-32.5	0.800	-24.8	0.880	177.6
7.50	0.910	145.4	0.004	-21.7	0.770	-27.5	0.880	175.5
7.75	0.910	143.4	0.004	-10.4	0.740	-30.2	0.890	173.4
8.00	0.910	141.5	0.004	0.2	0.720	-33.0	0.890	171.4
8.25	0.910	139.5	0.005	8.8	0.690	-35.7	0.890	169.3
8.50	0.900	137.5	0.005	15.4	0.670	-38.4	0.890	167.2
8.75	0.900	135.4	0.006	20.0	0.650	-41.1	0.890	165.2
9.00	0.900	133.3	0.007	23.2	0.630	-43.9	0.890	163.1
9.25	0.900	131.1	0.008	25.2	0.620	-46.6	0.900	161.0
9.50	0.900	128.8	0.009	26.3	0.600	-49.4	0.900	158.9
9.75	0.890	126.5	0.010	26.7	0.590	-52.2	0.900	156.8
10.00	0.890	124.2	0.011	26.6	0.580	-55.0	0.900	154.6
10.25	0.890	121.7	0.012	26.1	0.570	-57.8	0.900	152.5
10.50	0.880	119.2	0.014	25.2	0.560	-60.7	0.900	150.3
11.00	0.880	113.9	0.016	22.6	0.540	-66.6	0.900	145.8

These values are given in the reference plane defined by the connection between the transistor leads and the PCB according to the footprint previously mentioned

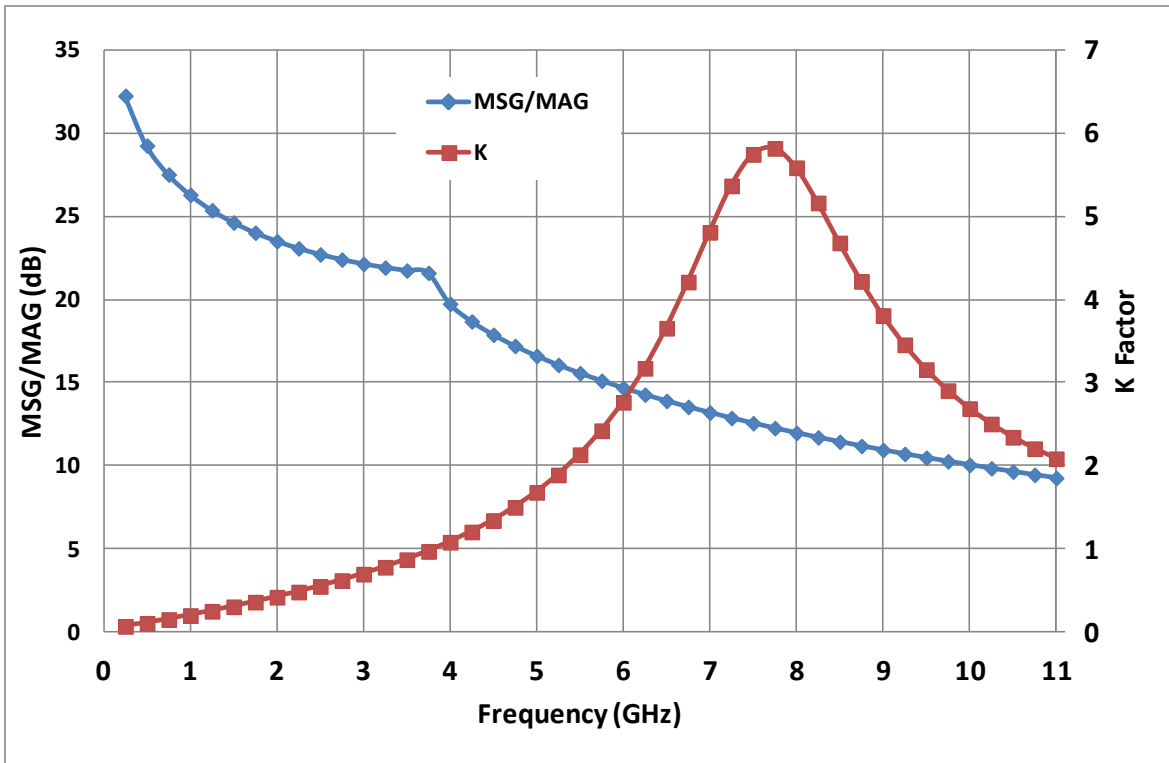
Typical Simulated S-parameters

T_{case} = +25°C. CW mode. V_{DS}=50V. I_{D_Q}=100mA.



Simulated Maximum Gain & Stability Characteristics

T_{case}= +25°C. CW mode. V_{DS}=50V. I_{DQ}=100mA

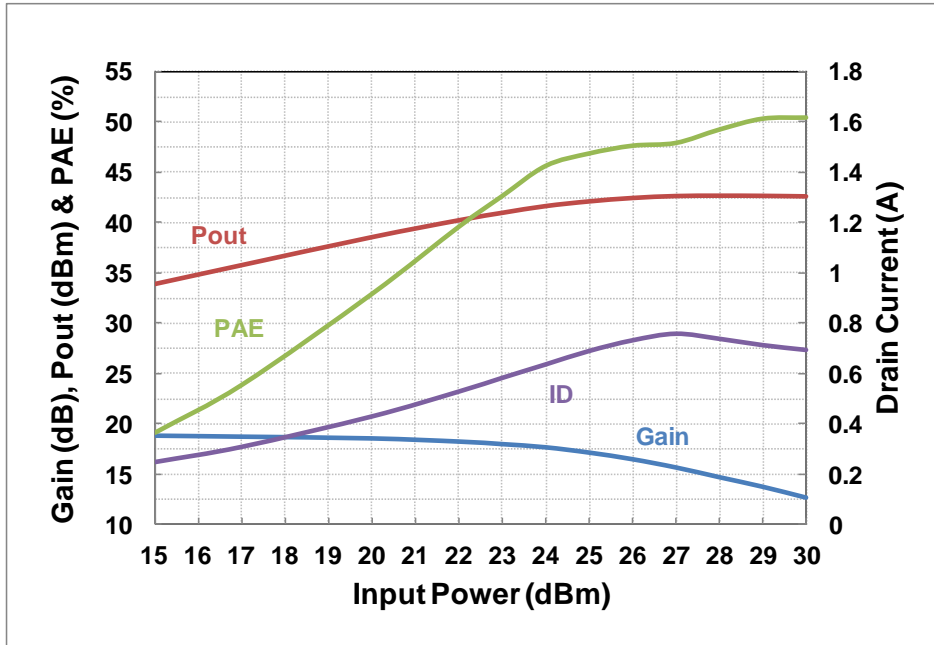


Typical Performance on Evaluation Board (ref 61502522)

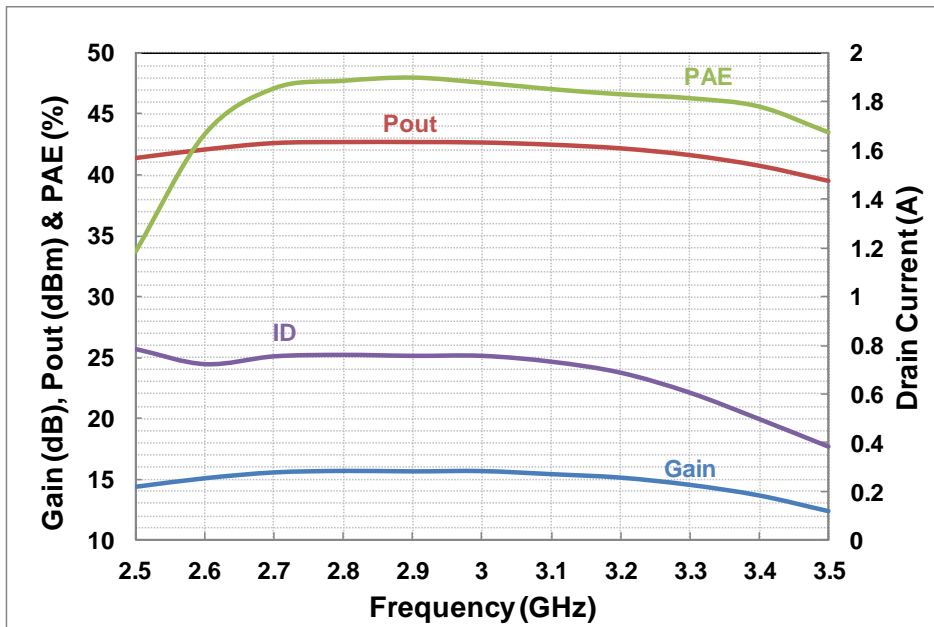
Calibration and measurements are done on the connector access planes of the evaluation boards.

Tamb. = +25°C. Pulsed Mode ⁽¹⁾. V_{DS}=50V. I_{D_Q}=100mA

Pout. PAE. Gain & ID @ Freq=2.9GHz



Pout. PAE. Gain & ID @ Pin=27dBm



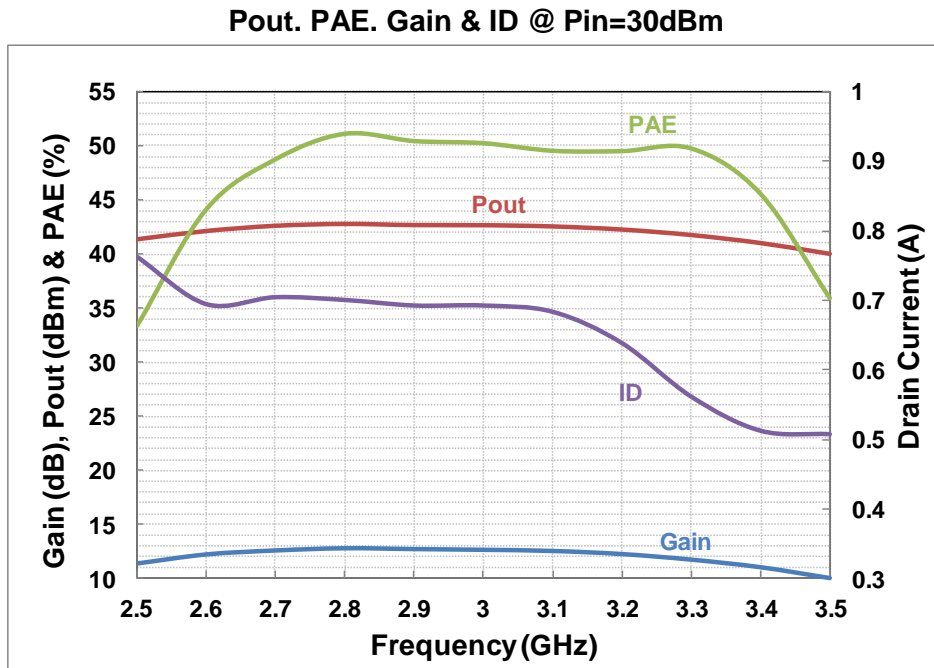
⁽¹⁾ Input RF and gate voltage are pulsed. Conditions are 100µs width. 10% duty cycle and 1µs offset between DC and RF pulse.



Typical Performance on Evaluation Board (ref 61502522)

Calibration and measurements are done on the connector access planes of the evaluation boards.

Tamb. = +25°C. Pulsed Mode ⁽¹⁾. V_{DS}=50V. I_{D,Q}=100mA



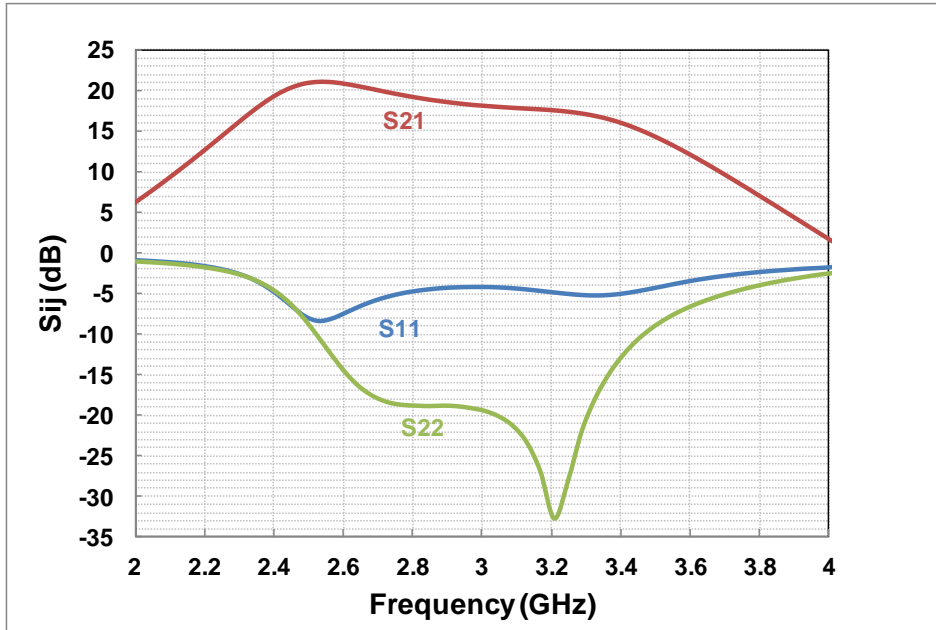
⁽¹⁾ Input RF and gate voltage are pulsed. Conditions are 100µs width. 10% duty cycle and 1µs offset between DC and RF pulse.

Typical Performance on Evaluation Board (ref 61502522)

Calibration and measurements are done on the connector access planes of the evaluation boards.

Tamb. = +25°C. CW mode. V_{DS}=50V. I_{D,Q}=100mA

S parameters versus frequency

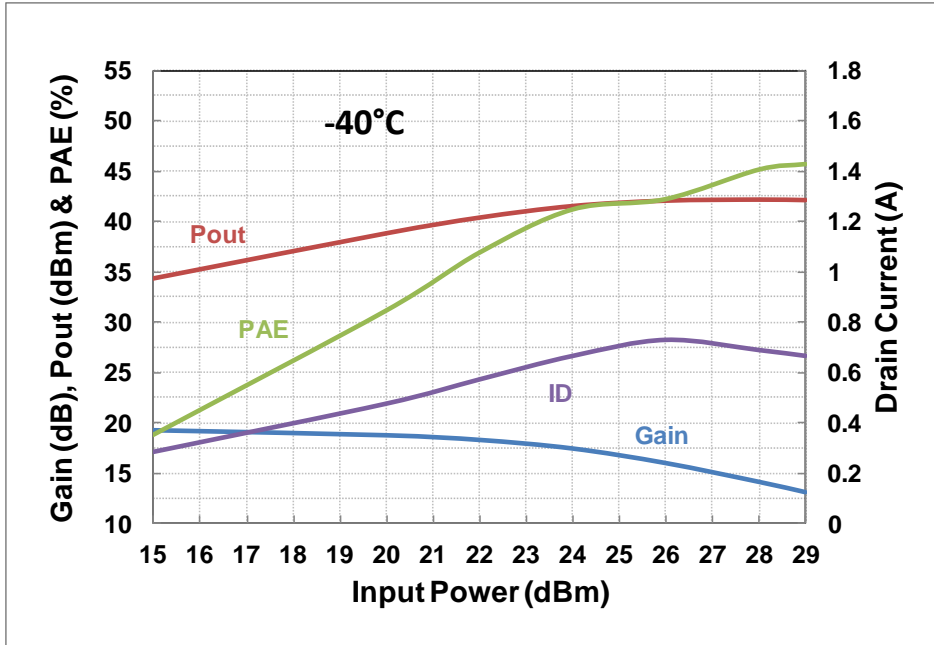


Typical Performance in Temperature (on Evaluation Board)

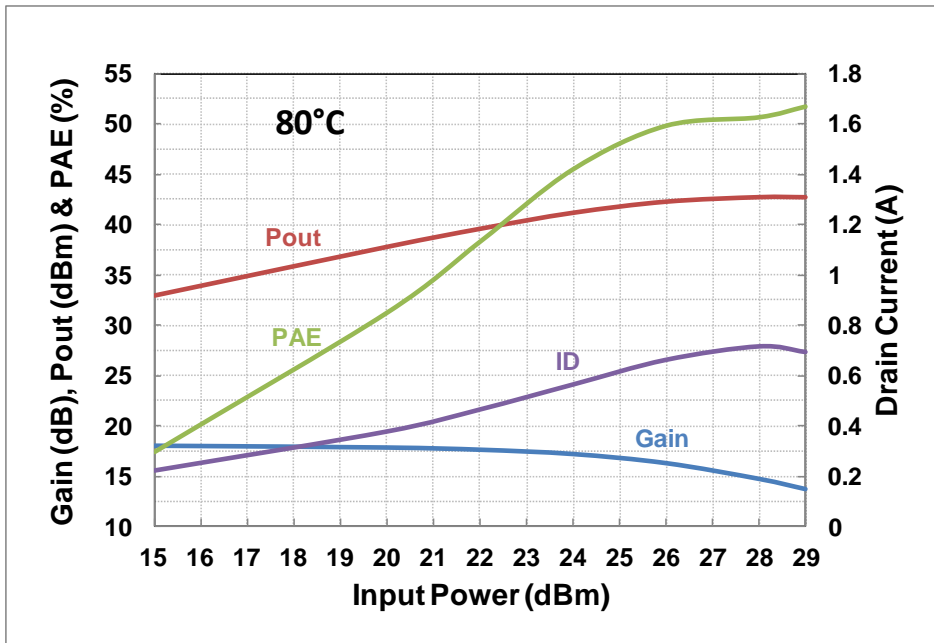
Calibration and measurements are done on the connector access planes of the evaluation boards.

Tamb. = -40°C, +80°C, Pulsed Mode ⁽¹⁾, V_{DS}=50V, I_{D,Q}=100mA

Pout, PAE, Gain & Id @ 2.9GHz & -40°C



Pout, PAE, Gain & Id @ 2.9GHz & +80°C



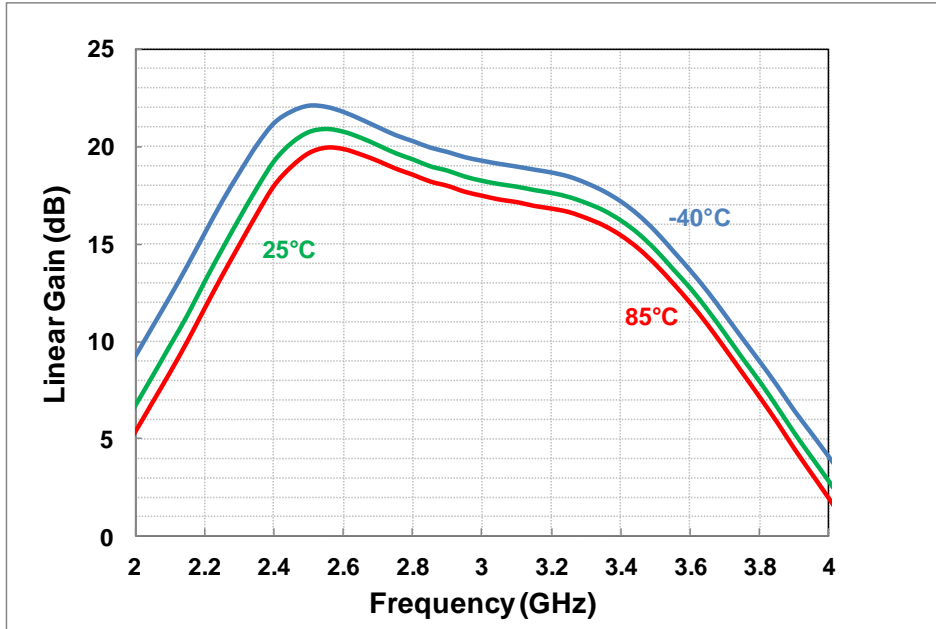
⁽¹⁾ Input RF and gate voltage are pulsed. Conditions are 100µs width, 10% duty cycle and 1µs offset between DC and RF pulse.

Typical Performance in Temperature (on Evaluation Board)

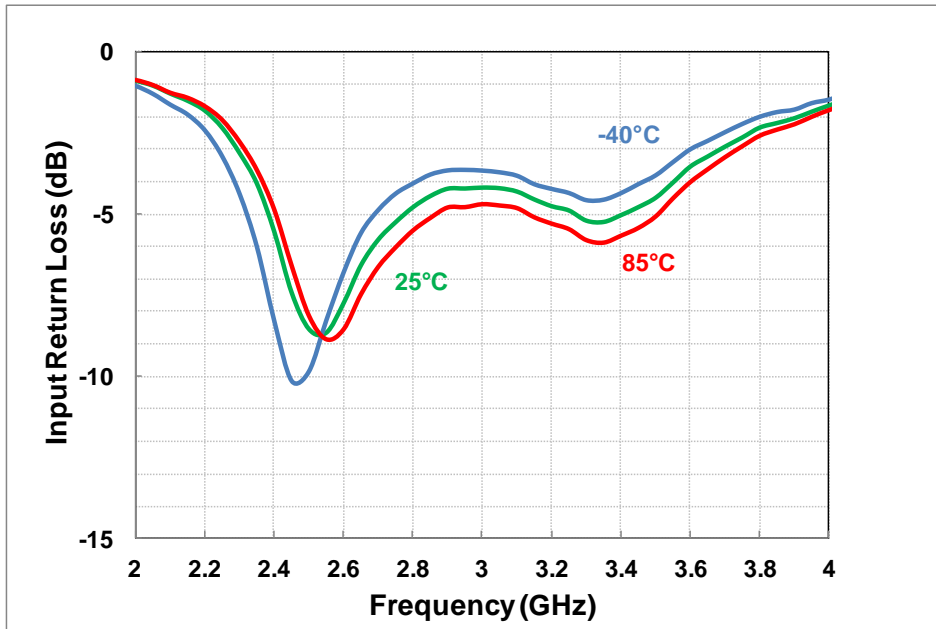
Calibration and measurements are done on the connector access planes of the evaluation boards.

Tamb. = -40°C, +25°C, +85°C, CW mode. $V_{DS}=50V$, $I_{D_Q}=100mA$ (fixed @ +25°C)

Linear Gain versus temperature with I_{D_Q} fixed @ each temperature (100mA)



Input Return Loss versus temperature with I_{D_Q} fixed @ each temperature (100mA)

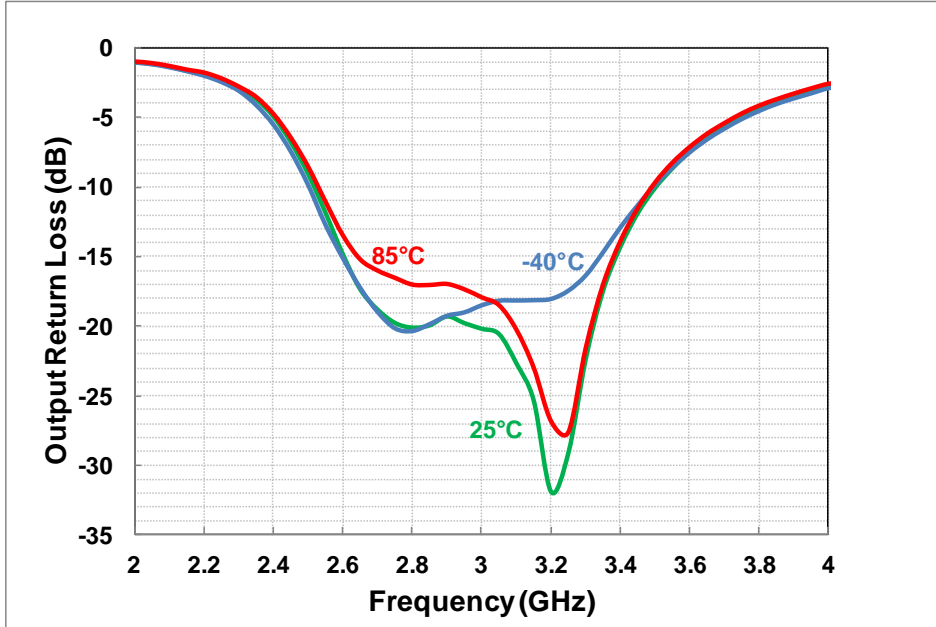


Typical Performance in Temperature (on Evaluation Board)

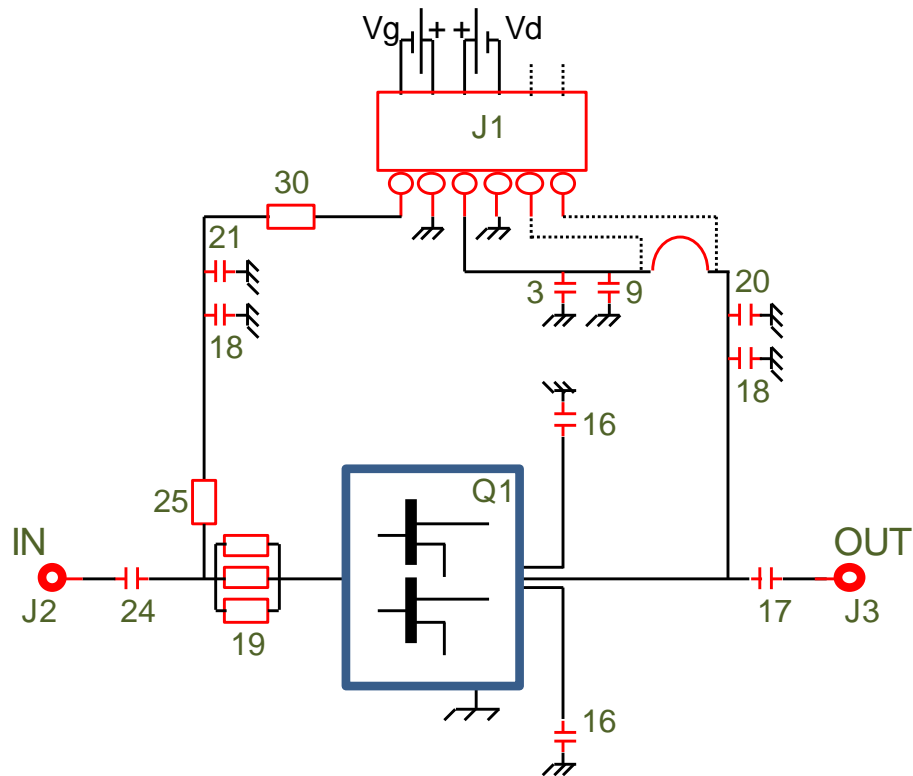
Calibration and measurements are done on the connector access planes of the evaluation boards.

Tamb. = -40°C, +25°C, +85°C, CW mode. VDS=50V, ID_Q=100mA (fixed @ +25°C)

Output Return Loss versus temperature with I_{D_Q} fixed @ each temperature (100mA)



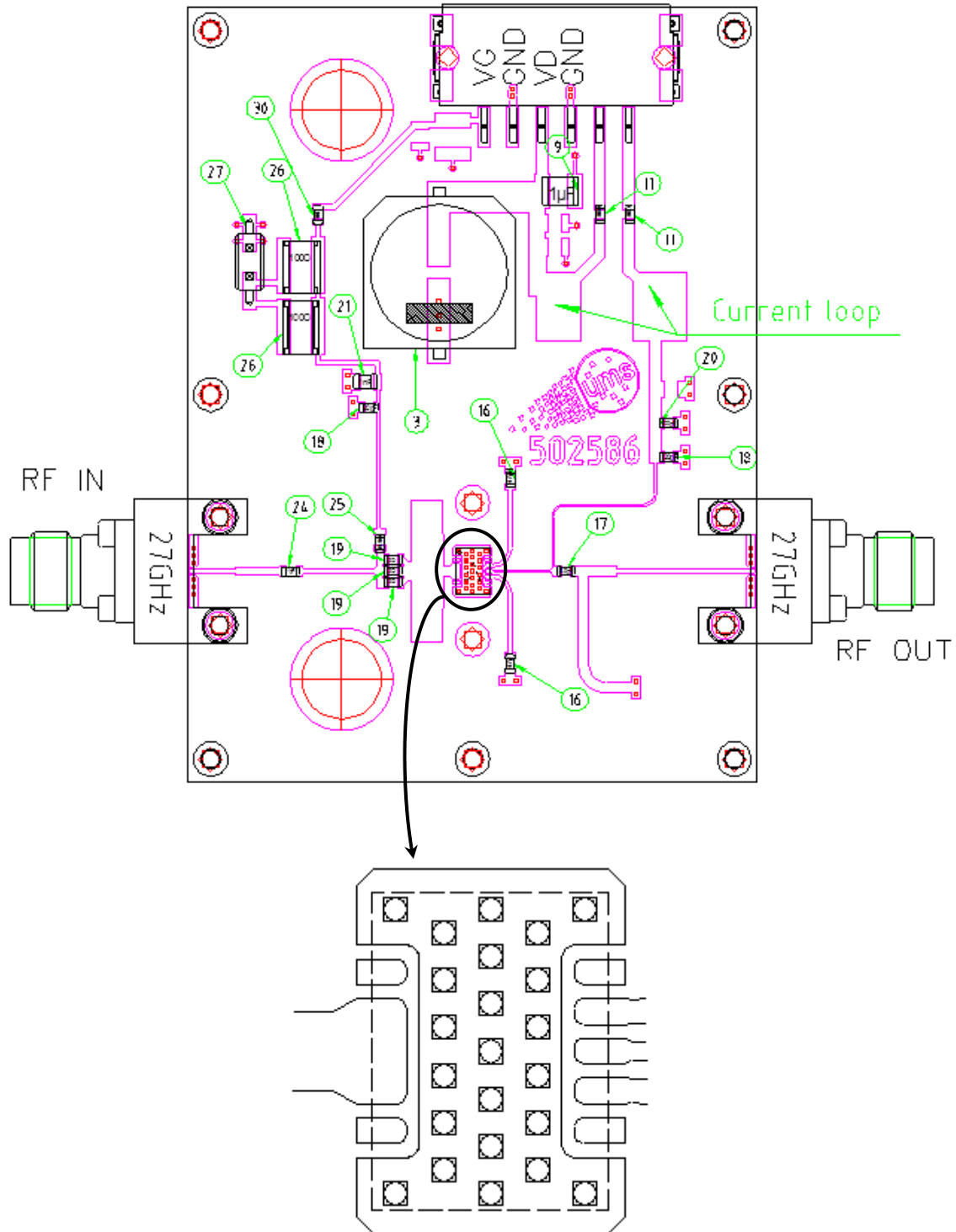
Demonstration Amplifier Low Frequency Equivalent Schematic (Ref. 61502522)



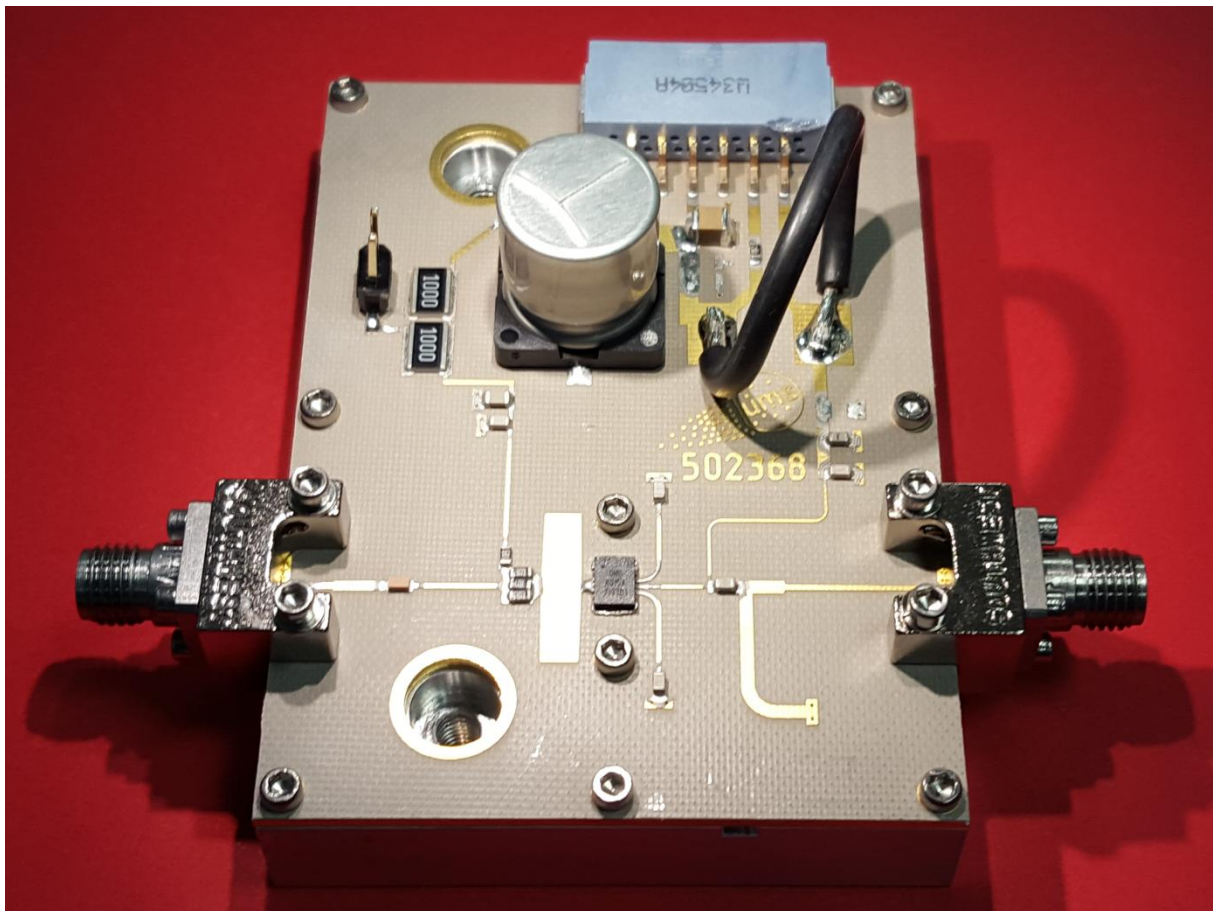
Demonstration Amplifier Bill of Materials (Ref. 61502522)

Designator	Type	Value - Description	Qty
24	Capacitor	1pF. +/- 0.1pF. 0603	1
16	Capacitor	4.7pF. +/- 0.25pF. 0603	1
17	Capacitor	3.9pF. +/- 0.25pF. 0603	1
18	Capacitor	20pF. +/- 5%. 0603	2
20	Capacitor	100pF. +/- 5%. 0603	1
21	Capacitor	1nF. +/- 5%. 0805	1
9	Capacitor	1μF. +/- 10%. 1210	1
3	Capacitor	68μF. +/- 20%	1
25	Resistor	49.9Ω. +/- 1%. 0603	1
19	Resistor	3Ω +/- 1%. 0603	3
30	Resistor	100Ω +/- 1%. 0603	1
J1	Connector	CMS 6cts	1
J2. J3	Connector	SMA	2
Q1	Packaged Transistor	CHK015A-QIA	1
-	PCB	TACONIC RF35P h=0.203mm	-

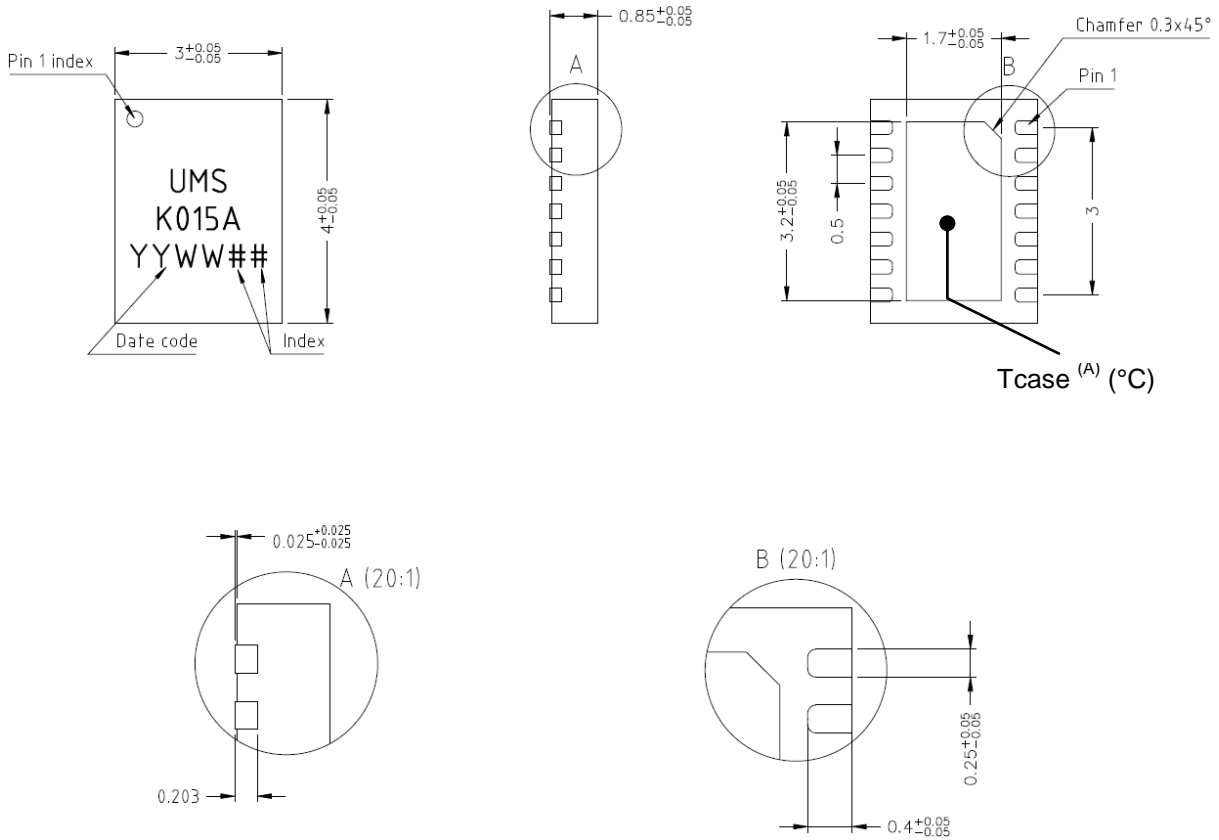
Demonstration Amplifier Circuit Outline (Ref. 61502522)



Demonstration Amplifier Circuit (Ref. 61502522)



Package outline



Matte tin. Lead Free	(Green)	1- Nc	6- Nc	11- D2
Units :	mm	2- Nc	7- Nc	12- D1
From the standard :	JEDEC MO-220	3- G1	8- Gnd	13- Nc
		4- G2	9- Nc	14- Gnd
		5- G3	10- D3	

^(A) Tcase locates the reference point used to monitor the device temperature. This point has been taken at the device / system interface to ease system thermal design.

Notes



Recommended package footprint

Refer to the application note AN0017 available at <http://www.ums-gaas.com> for package footprint recommendations.

SMD mounting procedure

For the mounting process standard techniques involving solder paste and a suitable reflow process can be used. For further details, see application note AN0017.

Recommended environmental management

UMS products are compliant with the regulation in particular with the directives RoHS N°2011/65 and REACH N°1907/2006. More environmental data are available in the application note AN0019 also available at <http://www.ums-gaas.com>.

Recommended ESD management

Refer to the application note AN0020 available at <http://www.ums-gaas.com> for ESD sensitivity and handling recommendations for the UMS package products.

Ordering Information

DFN 3x4 package:

CHK015A-QIA/XY

Stick: XY = 20

Tape & reel: XY = 21

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